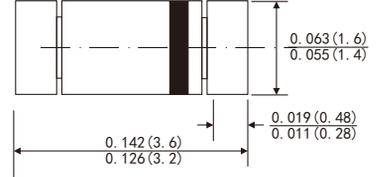


FEATURES

- For general purpose applications
- These diodes features very low turn-on voltage and fast switching.
- These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
- This diode is also available in the DO-35 glass case with type designation LL85.
- High temperature soldering guaranteed:260°C/10 seconds at terminals
- Component in accordance to RoHS 2011/65/EU

MiniMELF



MECHANICAL DATA

- Case: MiniMELF glass case
- Polarity: color band denotes cathode end
- Weight: Approx. 0.05 gram

Dimensions in inches and (millimeters)

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Repetitive Peak Reverse Voltage	V _R	30	V
Forward Continuous Current at T _A =25°C	I _F	200 ¹⁾	mA
Repetitive Peak Forward Current at t _κ ≤ 1s, κ ≤ 0.5, T _A =25°C	I _{FM}	300 ¹⁾	mA
Surge forward current at t _p < 10ms, T _A =25°C	I _{FSM}	5 ¹⁾	A
Power Dissipation at T _A =65°C	P _{tot}	200 ¹⁾	mW
Junction temperature	T _J	125	°C
Ambient Operating temperature Range	T _A	-65 to +125	°C
Storage Temperature Range	T _{STG}	-65 to +150	°C

1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Units
Reverse breakdown voltage Tested with 100μA pulses	V _{(BR)R}	30			V
Forward voltage Pulse Test t _p < 300μs, δ < 2% at I _F =0.1mA, at I _F =1mA, at I _F =10mA, at I _F =30mA, at I _F =100mA	V _F			0.24 0.32 0.40 0.50 0.80	V
Leakage current V _R =25V	I _R			2.3	μA
Junction Capacitance at V _R =1V, f=1MHz	C _J			10	pF
Reverse recovery time Form I _F =10mA, I _R =10mA, I _R =1mA	t _{rr}			4	ns
Thermal resistance junction to ambient Air	R _{θJA}			320	K/W